

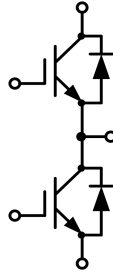
34mm Half Bridge IGBT Module

电气特性:

- 1200V 沟槽栅/场终止工艺
- 低开关损耗
- 正温度系数

典型应用:

- 逆变焊机



$V_{CES}=1200V$, $I_{C\ nom}=50A$ / $I_{CRM}=100A$

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
集电极-发射极电压 Collector-Emitter voltage	$T_{vj}=25^{\circ}C$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C=100^{\circ}C$, $T_{vj\ max}=175^{\circ}C$	$I_{C\ nom}$	50	A
集电极重复峰值电流 Repetitive peak collector current	$t_p=1\ ms$	I_{CRM}	100	A
栅极-发射极电压 Gate emitter voltage		V_{GE}	± 20	V

特征值 / Characteristic Values

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
集电极-发射极饱和电压 Collector-Emitter saturation voltage	$V_{GE}=15V$, $I_C=50A$ $T_{vj}=25^{\circ}C$ $V_{GE}=15V$, $I_C=50A$ $T_{vj}=125^{\circ}C$ $V_{GE}=15V$, $I_C=50A$ $T_{vj}=150^{\circ}C$	V_{CEsat}		2.07 2.49 2.61	2.55	V
栅极-发射极阈值电压 Gate-Emitter threshold voltage	$I_C = 1.7mA$, $V_{GE}= V_{CE}$ $T_{vj}=25^{\circ}C$	$V_{GE(th)}$	5.20	5.70	6.30	
栅电荷 Gate charge	$V_{GE}=-15V \dots +15V$	Q_G		0.25		μC
内部栅极电阻 Internal gate resistor	$T_{vj}=25^{\circ}C$	R_{Gint}		2.75		Ω
输入电容 Input capacitance	$f=100KHz$, $V_{CE}=25\ V$, $V_{GE}=0\ V$ $T_{vj}=25^{\circ}C$	C_{ies}		2.98		nF
反向传输电容 Reverse transfer capacitance		C_{res}		0.12		

集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE}=1200V, V_{GE}=0V$ $T_{vj}=25^{\circ}C$	I_{CES}			1	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE}=0V, V_{GE}=20V$ $T_{vj}=25^{\circ}C$	I_{GES}			100	nA
开通延迟时间 Turn-on delay time	$I_C=50A, V_{CE}=600V$ $V_{GE}=\pm 15V, R_G=15\Omega$ (电感负载) / (inductive load) $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	$t_{d\ on}$		52 49 49		ns
上升时间 Rise time	$I_C=50A, V_{CE}=600V$ $V_{GE}=\pm 15V, R_G=15\Omega$ (电感负载) / (inductive load) $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	t_r		27 30 31		
关断延迟时间 Turn-off delay time	$I_C=50A, V_{CE}=600V$ $V_{GE}=\pm 15V, R_G=15\Omega$ (电感负载) / (inductive load) $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	$t_{d\ off}$		192 230 240		
下降时间 Fall time	$I_C=50A, V_{CE}=600V$ $V_{GE}=\pm 15V, R_G=15\Omega$ (电感负载) / (inductive load) $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	t_f		152 202 207		
开通损耗能量（每脉冲） Turn-on energy loss per pulse	$I_C=50A, V_{CE}=600V$ $V_{GE}=\pm 15V, R_G=15\Omega$ $di/dt = 1300A/\mu s$ ($T_{vj} =$ 150°C) (电感负载) / (inductive load) $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	E_{on}		3.26 5.19 5.94		mJ
关断损耗能量（每脉冲） Turn-off energy loss per pulse	$I_C=50A, V_{CE}=600V$ $V_{GE} = \pm 15V, R_G=15\Omega$ $dv/dt=5900V/\mu s$ ($T_{vj} =$ 150°C) (电感负载) / (inductive load) $T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	E_{off}		2.26 3.05 3.23		
短路数据 SC data	$V_{GE}\leq 15V, V_{CC}=800V$ $V_{CEmax}=V_{CES}-L_{sCE}\cdot di/dt$ $t_p\leq 10\mu s, T_{vj}=150^{\circ}C$	I_{SC}		262		A
在开关状态下温度 Temperature under switching conditions		$T_{vj\ op}$	-40		150	$^{\circ}C$

二极管，逆变器 / Diode, Inverter

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj}=25^{\circ}C$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	50	A
正向重复峰值电流 Repetitive peak forward current	$t_p=1ms$	I_{FRM}	100	A
I^2t 值 I^2t -value	$t_p=10ms, \sin 180^{\circ}, T_{vj}=125^{\circ}C$	I^2t	490	A^2s

特征值 / Characteristic Values

Parameter	Conditions		Symbol	Value			Unit
				Min.	Typ.	Max.	
正向电压 Forward voltage	$I_F=50A, V_{GE}=0V$ $I_F=50A, V_{GE}=0V$ $I_F=50A, V_{GE}=0V$	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	V_F		2.11 1.85 1.75	2.60	V
反向恢复峰值电流 Peak reverse recovery current	$I_F=50A,$ $-di_F/dt=800A/\mu s(T_{vj}=150^{\circ}C)$ $V_R=600V, V_{GE}=-15V$	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	I_{RM}		59 83 90		A
恢复电荷 Recovered charge	$I_F=50A,$ $-di_F/dt=1300A/\mu s(T_{vj}=150^{\circ}C)$ $V_R=600V, V_{GE}=-15V$	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	Q_r		2.01 6.53 8.91		μC
反向恢复损耗（每脉冲） Reverse recovered energy	$I_F=50A,$ $-di_F/dt=1300A/\mu s(T_{vj}=150^{\circ}C)$ $V_R=600V, V_{GE}=-15V$	$T_{vj}=25^{\circ}C$ $T_{vj}=125^{\circ}C$ $T_{vj}=150^{\circ}C$	E_{rec}		0.34 1.67 2.69		mJ
在开关状态下温度 Temperature under switching conditions			$T_{vj\ op}$	-40		150	$^{\circ}C$

模块 / Module

Parameter	Conditions	Symbol	Value			Unit
绝缘测试电压 Isolation test voltage	RMS, f=50Hz, t=1min	V_{ISOL}	2500			V
内部绝缘 Internal isolation			Al_2O_3			
储存温度 Storage temperature		T_{stg}	-40		125	$^{\circ}C$
模块安装的扭矩 Mounting torque for modul mounting		M	3.0		5.0	Nm
端子连接扭矩 Terminal Connection Torque		M	2.5		5.0	Nm
重量 Weight		W		150		g

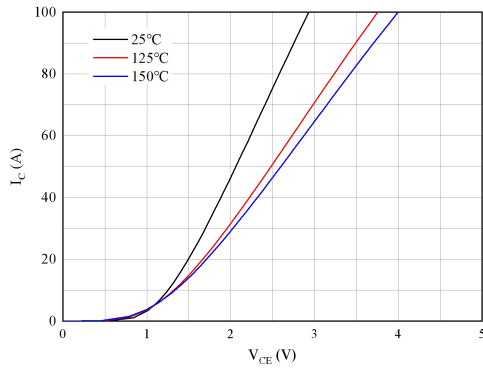
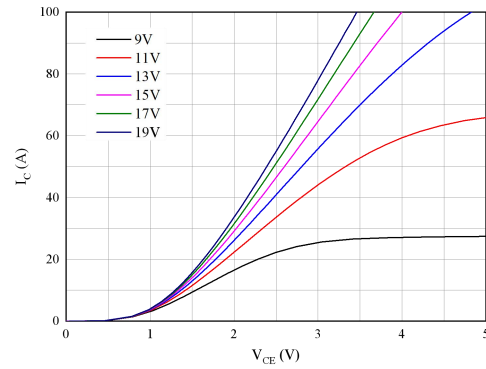
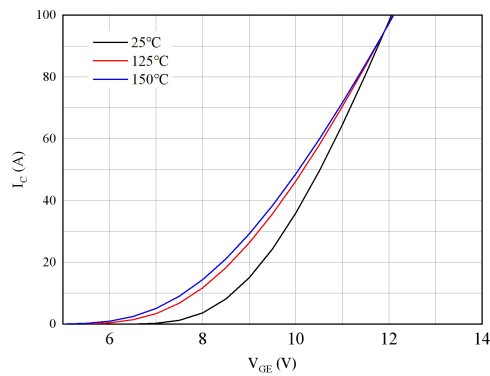
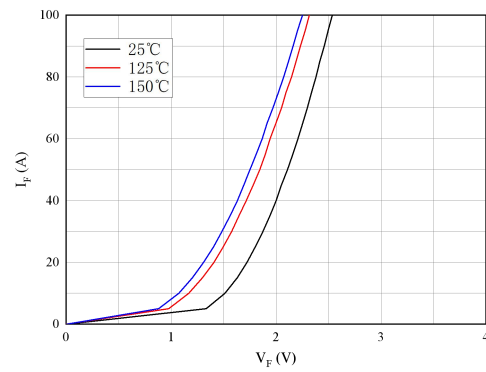
图 1. 典型输出特性 ($V_{GE}=15V$)Figure 1. Typical output characteristics ($V_{GE}=15V$)图 2. 典型输出特性 ($T_{vj}=150^{\circ}C$)Figure 2. Typical output characteristics ($T_{vj}=150^{\circ}C$)图 3. 典型传输特性 ($V_{CE}=20V$)Figure 3. Typical transfer characteristic ($V_{CE}=20V$)

图 4. 正向偏压特性 二极管

Figure 4. Forward characteristic of Diode

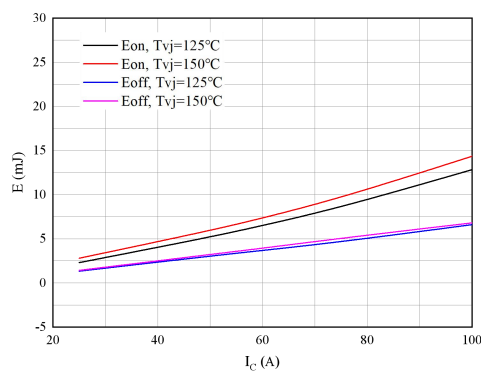


图 5. 开关损耗 逆变器

Figure 5. Switching losses of IGBT

$V_{GE}=\pm 15V$, $R_{Gon}=15\Omega$, $R_{Goff}=15\Omega$, $V_{CE}=600V$

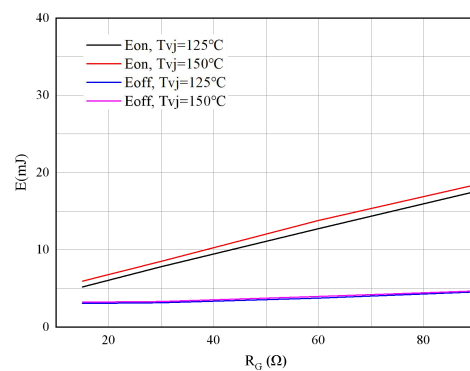


图 6. 开关损耗 逆变器

Figure 6. Switching losses of IGBT

$V_{GE}=\pm 15V$, $I_C=50A$, $V_{CE}=600V$

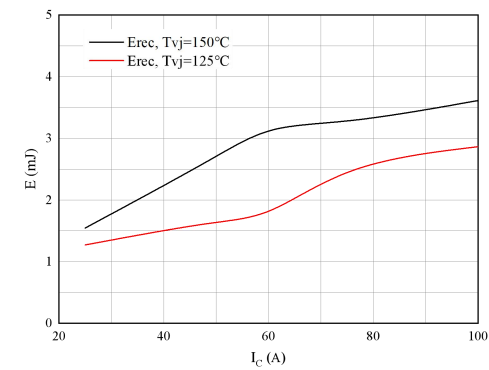


图 7. 开关损耗 二极管
Figure 7. Switching losses of Diode
 $R_{Gon}=15 \Omega$, $V_{CE}=600V$

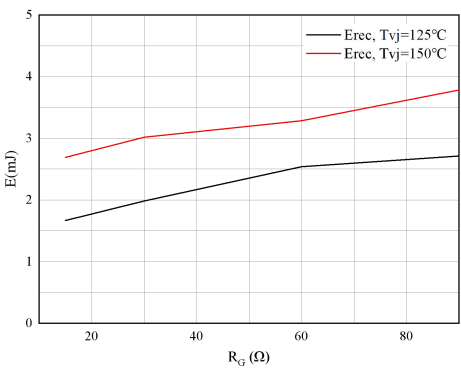


图 8. 开关损耗 二极管
Figure 8. Switching losses of Diode
 $I_F=50A$, $V_{CE}=600V$

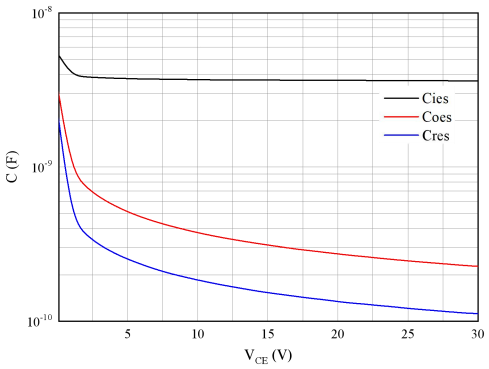
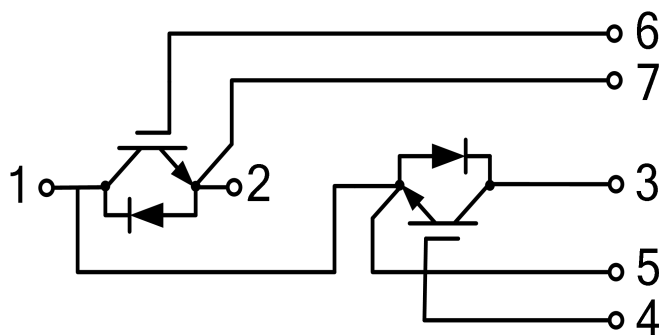


图 9. 电容特性
Figure 9. Capacitance characteristic

接线图 / Circuit diagram



封装尺寸 / Package outlines

